

1 ASSOCIATE CONTENT

2 Supporting Information

3 **Sensitized Solar Cells with Colloidal PbS/CdS Core/Shell**
4 **Quantum Dots**

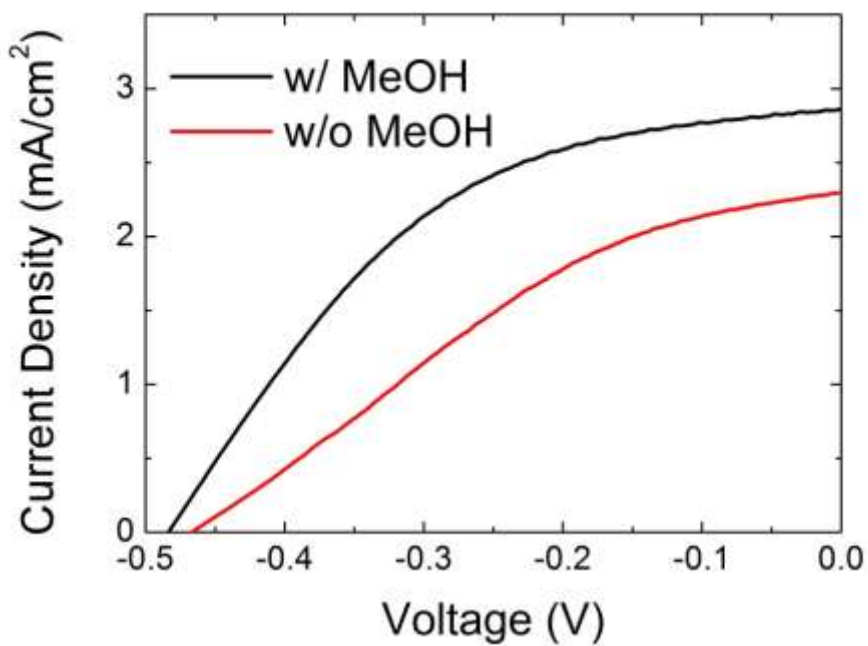
5 Lai-Hung Lai,^a Loredana Protesescu,^{b,c} Maksym V. Kovalenko^{b,c} and Maria Antonietta Loi^a

6 ^aZernike Institute for Advanced Materials, University of Groningen, Nijenborgh 4, Groningen, 9747 AG, The Netherlands

7 ^bDepartment of Chemistry and Applied Biosciences, ETH Zürich, Wolfgang-Pauli-Str. 10, Zurich, 8093, Switzerland

8 ^cEMPA-Swiss Federal Laboratories for Materials Science and Technology, Überlandstrasse 129, Dübendorf, 8600, Switzerland

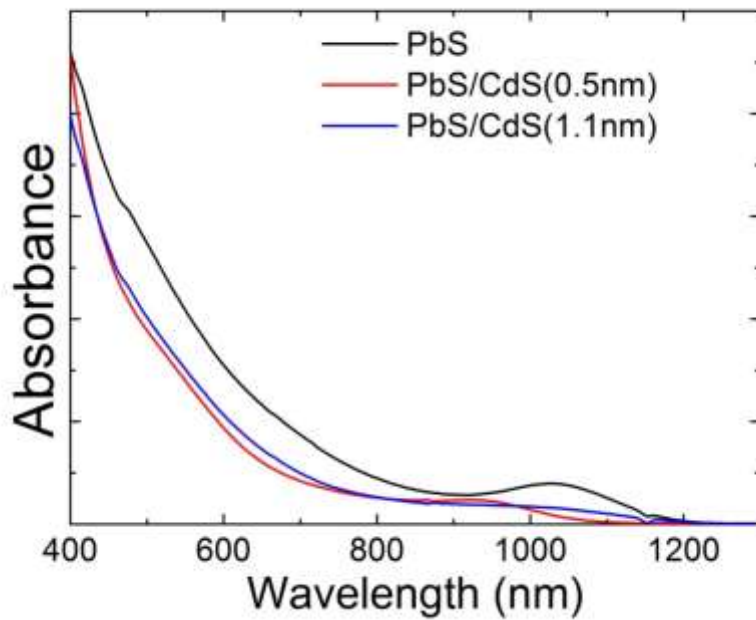
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11 **Figure S1.** PbS/CdS (1.1 nm) QD sensitized solar cells in the polysulfide
12 electrolyte with and without methanol.

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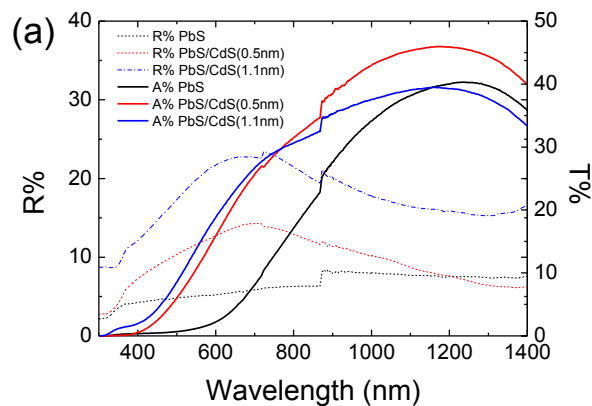


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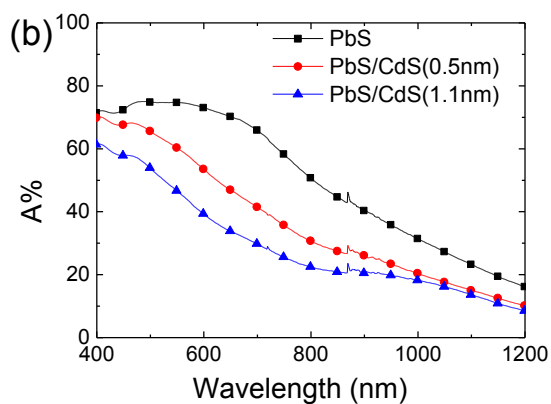
15 **Figure S2.** Absorbance of oleic-acid passivated colloidal QDs in chloroform.

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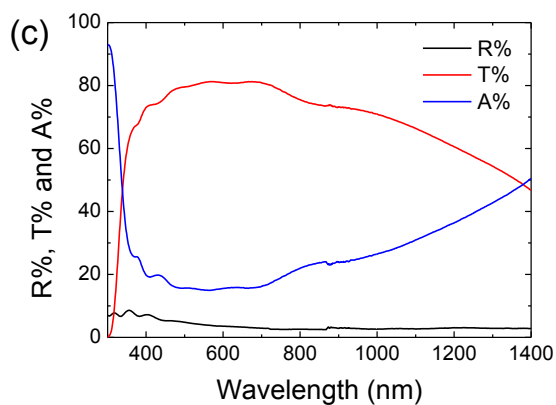
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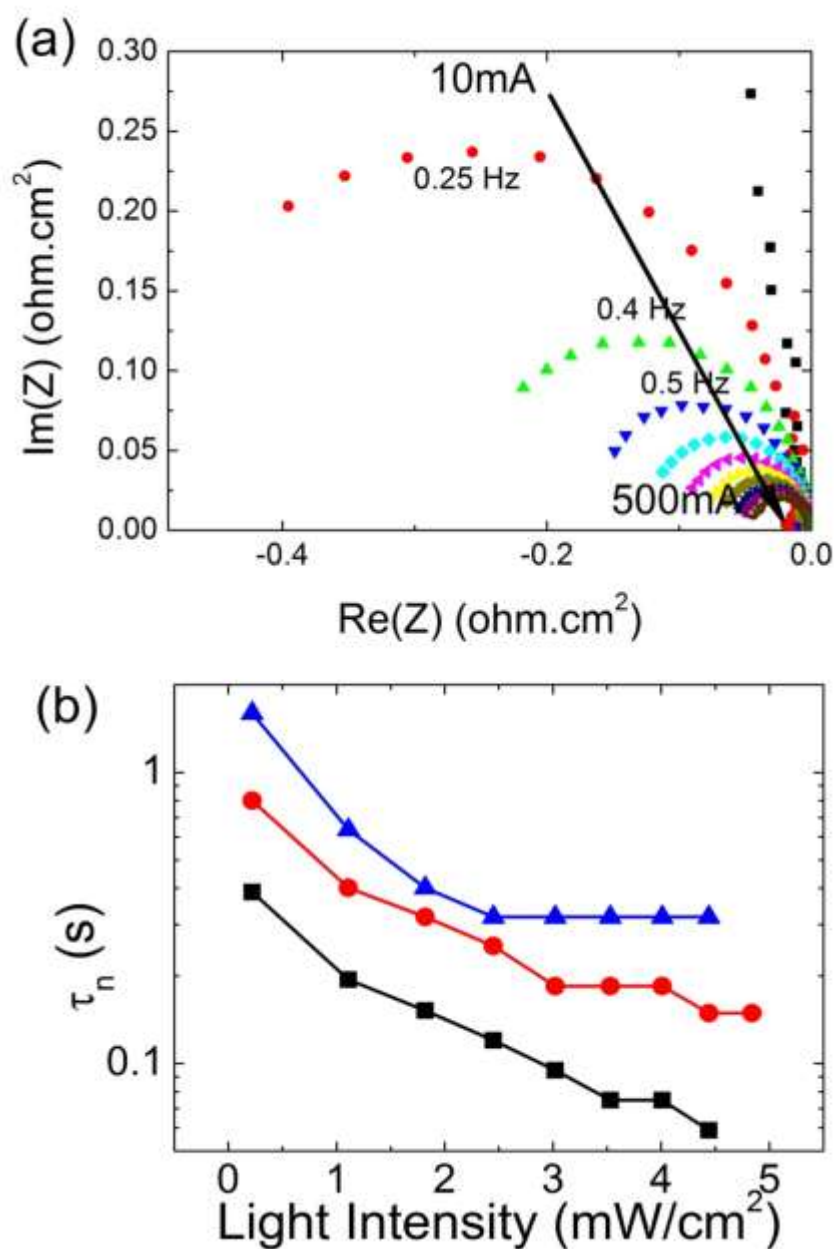


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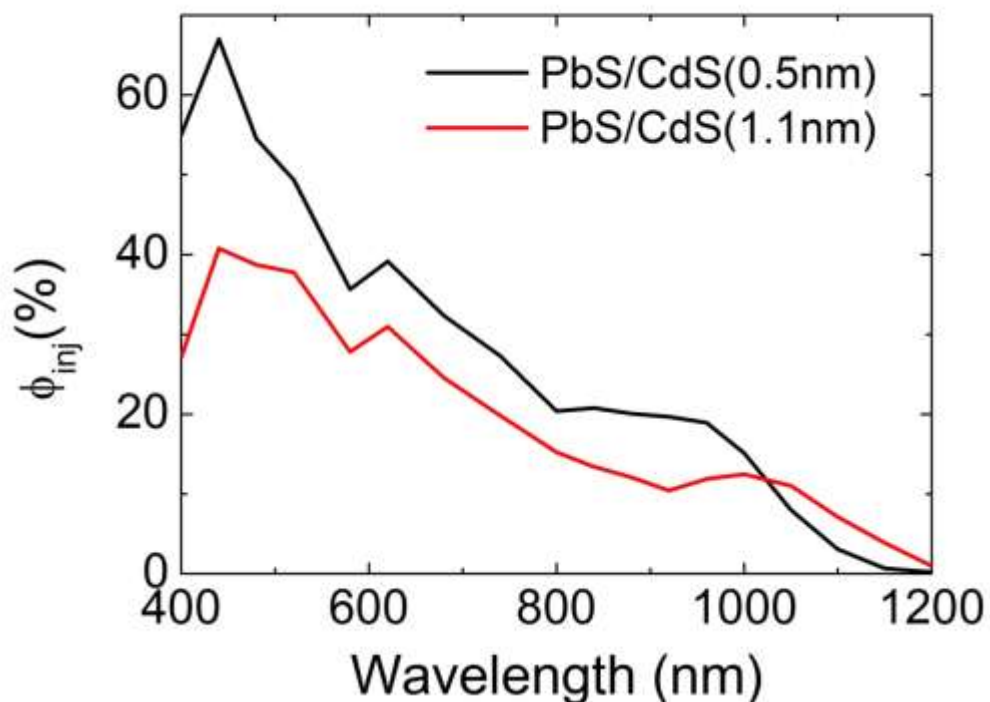


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21 **Figure S3.** (a) Reflectance and transmittance of QD sensitized electrodes
22 (Glass/FTO/TiO₂/QDs) (b) Absorbance spectra of QD sensitized electrodes
23 (TiO₂/QDs) (c) Reflection, transmission and absorption of Glass/FTO substrate.



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25 **Figure S4.** (a) Nyquist plot of IMVS spectra of PbS/CdS(1.1nm) QD sensitized
26 solar cells, measured by employing a 528 nm LED, scanned from 10 mA
27 (corresponding to 0.22mW/cm² light intensity) to 500 mA (corresponding to 5.57
28 mW/cm² light intensity). (b) Light intensity dependent mean electron lifetime
29 determined by IMVS measured under 528 nm LED illumination.



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31 **Figure S5.** Charge injection efficiencies for cells with different CdS shell
32 thicknesses. The charge injection efficiency is obtained by $\phi_{inj} = IQE/\eta_c$, where
33 the η_c is measured at 10 mW/cm^2 (Table S1) is used.

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36 **Table S1.** Equivalent circuit fitting results and other parameters of cells ^a

Light Intensity	C_{μ}^b	R_{ct}^c	R_r^d	τ_n^e	τ_d^f	D_e^g	μ_e^h	L_d^i	η_e^j
$mWcm^{-2}$	$\mu Fcm^{-2}\mu m^{-1}$	$\Omega cm^2\mu m^{-1}$	$\Omega cm^2\mu m$	ms	ms	m^2s^{-1}	$cm^2V^{-1}s^{-1}$	μm	%
PbS									
100.0	358.08	32.19	109.68	39.27	5.94E+02	2.69E-11	1.05E-05	1.0	31.7
91.2	170.53	31.38	155.68	26.55	3.36E+02	4.76E-11	1.85E-05	1.1	34.2
79.4	166.65	38.34	158.96	26.49	4.02E+02	3.98E-11	1.55E-05	1.0	31.7
50.1	180.79	63.98	199.20	36.01	6.76E+02	2.37E-11	9.21E-06	0.9	29.0
31.6	189.94	103.13	291.92	55.45	9.42E+02	1.70E-11	6.61E-06	1.0	31.7
10.0	132.69	161.50	960.00	127.38	2.69E+03	5.94E-12	2.31E-06	0.9	29.0
PbS/CdS(0.5nm)									
100.0	315.79	1.58	130.00	41.05	4.90E+01	3.27E-10	1.27E-04	3.7	75.6
91.2	316.45	1.33	139.00	43.99	3.86E+01	4.15E-10	1.62E-04	4.3	82.3
79.4	314.59	1.87	208.00	65.43	4.55E+01	3.51E-10	1.37E-04	4.8	84.5
50.1	361.82	1.39	155.00	56.08	7.21E+01	2.22E-10	8.64E-05	3.5	74.2
31.6	356.04	2.41	292.00	103.96	8.36E+01	1.91E-10	7.45E-05	4.5	83.1
10.0	367.23	3.30	610.00	224.01	1.10E+02	1.46E-10	5.68E-05	5.7	88.2
PbS/CdS(1.1nm)									
100.0	892.45	0.26	195.20	174.21	2.13E+01	7.50E-10	2.92E-04	11.4	96.6
91.2	891.09	0.38	222.40	198.18	3.48E+01	4.60E-10	1.79E-04	9.5	95.2
79.4	880.38	0.42	253.76	223.41	3.38E+01	4.74E-10	1.84E-04	10.3	95.9
50.1	847.88	0.45	397.84	337.32	3.65E+01	4.38E-10	1.71E-04	12.2	97.0
31.6	817.18	0.51	606.40	495.54	4.29E+01	3.73E-10	1.45E-04	13.6	97.6
10.0	718.56	0.56	1312.80	943.32	4.28E+01	3.74E-10	1.45E-04	18.8	98.7

37 ^a values are determined based on the data measured at open-circuit condition under different light intensity by transmission line
 38 model fitting as the equivalent circuit shown in Fig. 3a.

39 ^b the chemical capacitance per cm^2 produced by the accumulation of electrons in the TiO_2 and interface, $C_{\mu}' (= c_{\mu}'L)$, where L is
 40 the thickness of the TiO_2 . $C_{\mu} = Q(2\pi f_p)^{\alpha-1}$, where Q is constant phase element (CPE), α is a constant, and f_p is the peak frequency
 41 of Nyquist impedance plots.

42 ^c electron transport resistance, $R_{ct}' (= r_{ct}'L)$

43 ^d interfacial charge recombination resistance, $R_r' (= r_r'/L)$

44 ^e the average electron lifetime in TiO₂, $\tau_n = C'_\mu R'_r$

45 ^f the average electron transit time, $\tau_d = L^2/D_e$

46 ^g electron diffusion coefficient, $D_e = (r_r/r_{ct})L^2/(2\pi\tau_n)$

47 ^h electron mobility, $\mu_e = D_e/k_B T$

48 ⁱ electron diffusion length, $L_d = (\tau_n D_e)^{0.5}$

49 ^j charge collection efficiency^{S1-S3}, $\eta_c = \frac{(-L_d \alpha \cosh(\frac{L}{L_d}) + \sinh(\frac{L}{L_d}) + L_d \alpha e^{-\alpha L}) L_d \alpha}{(1 - e^{-\alpha L})(1 - L_d^2 \alpha^2) \cosh(\frac{L}{L_d})}$, where α is the extinction coefficient of quantum

50 dot-sensitized TiO₂ film. Here we assume the αL equals to 1 for the calculation. Another well-adopted formula for the charge

51 collection efficiency is $\eta_c = 1 - (\frac{L}{L_d})^2$. However, it is only valid when the cell active layer is thin enough so that the

52 photo-generated electrons either immediately transport to the electrodes or recombine. In the case $L=L_d$ results in $\eta_c = 0$,
53 indicating this formula obviously deviates the real situation of the quantum dot-sensitized solar cells.

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55 Supplementary References

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